

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,897,542 B2
DATED : May 24, 2005
INVENTOR(S) : Charles H. Dennison

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [56], **References Cited**, U.S. PATENT DOCUMENTS, replace
"6,097,677 A 8/2000 Wu" with -- 6,087,677 A 7/2000 Wu --.

Column 3,

Line 26, replace "nitride (Si_3N) or silicon oxynitride ($\text{Si}_x\text{O}_y\text{N}_z$, wherein x, y" with
-- nitride (Si_3N_4) or silicon oxynitride ($\text{Si}_x\text{O}_y\text{N}_z$, wherein x, y --.

Column 6,

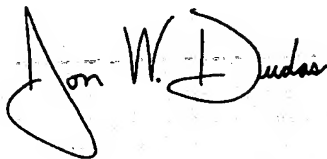
Line 36, replace "throughto the first diffusion region and having a second" with
-- through to the first diffusion region and having a second --.

Column 8,

Line 16, replace "with the planar uppermost surface. of the insulative" with
-- with the planar uppermost surface of the insulative --.

Signed and Sealed this

Fourth Day of April, 2006

A handwritten signature in black ink, reading "Jon W. Dudas". The signature is stylized, with the first name "Jon" and last name "Dudas" clearly legible, and the middle initial "W." in between. The signature is written over a faint, dotted rectangular box.

JON W. DUDAS
Director of the United States Patent and Trademark Office